F	
<sup>م</sup>	
. <u></u>	=
5 N	
這	
20	
	_
50	
2	
Ξ.	

PATENT	NL	IMBER and	
1221	1E	DATE	

## U.S. UTILITY Patent Application

10010162 11/20/2001 438	APPL NUM	FILING DATE	CLASS	, ,	GAU	EXAMINER	
**FOREIGN APPLICATIONS VERIFIED: New AR Col3d c 3  PG-PUB DO NOT PUBLISH RESCIND RESCIND ATTORNEY DOCKET NO SUSC 119 conditions met Per 3 up s = no Verified and Acknowledged Examiners's initials No Color Substrates	10010162	11/20/2001	438	400	2812	ROMAN, A	
PG-PUB DO NOT PUBLISH ☐ RESCIND ☐  Foreign priority claimed ☐ yes ☐ no 35 USC 119 conditions met ☐ yes ☐ no  Verified and Acknowledged Examiners's initials ☐ Yes ☐ GS 149  TITLE: Method of forming narrow trenches in semiconductor substrates	**APPLICANT	S: Hshieh	Fwu-luan	; So Koon; Am	nato John	n; Pratt Brian;	
Foreign priority claimed							
35 USC 119 conditions met  Verified and Acknowledged Examiners's initials  Directo/3c/c3  GS 149  TITLE: Method of forming narrow trenches in semiconductor substrates			□ yes			ATTORNEY DOCKET NO	
TITLE : Method of forming narrow trenches in semiconductor substrates	35 USC 119 condit	ons met	□ yes	□ no		Į	(
	Vermed and Advisowedged Examiners 5 milars N7 Ctb/3c103						

NOTICE OF ALL	OWANCE MAILED		CLAIMS ALLOWED			
-		Assistant Examiner	Total Claims	Pri O.	nt Claim for G	
ISSUE FEE		<b>T</b>	DRAWING			
Amount Due	Date Paid		Sheets Drwg.	Figs.Drwg.	Print Fig.	
<u> </u>	<u> </u>	Primary Examiner	ì		_1	
TER	RMINAL	PREPARED FOR ISSUE	Applicati n Examiner			
	DISCLAMER	WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.				

FILED WITH:	DISK (CRF)	CD-ROI
	(Attached in pocke	t on right inside fla